



60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE LOW-SIDE INTELLIFET

Product Summary

V _{DS}	R _{DS(ON)}	E _{AS}	I _D T _A = +25°C
60V	500mΩ	120mJ	1.3A

Description

The ZXMS6004N8Q is a self-protected low side IntelliFET® with logic level input. It integrates over-temperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004N8Q is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

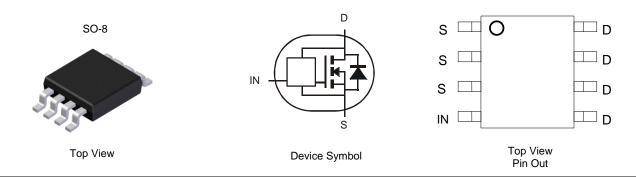
- Especially Suited for Loads with a High In-rush Current Such As Lamps and Motors
- All types of resistive, inductive and capacitive loads in switching applications
- µC Compatible Power Switch for 12V and 24V DC Applications
- Replaces electromechanical relays and discrete circuits
- Linear Mode capability the current-limiting protection circuitry is designed to de-activate at low V_{DS} to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low VDS.

Features and Benefits

- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Overvoltage Protection (active clamp)
- Thermal Shutdown with Auto Restart
- **Overcurrent Protection**
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Characterized to AEC-Q101-006 Grade E for Short-circuit Reliability
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 80.2mg (Approximate)



Ordering Information (Note 5)

	Part number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXMS6004N8Q-13	6004N8	13	12	2,500 units
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.				

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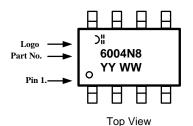
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

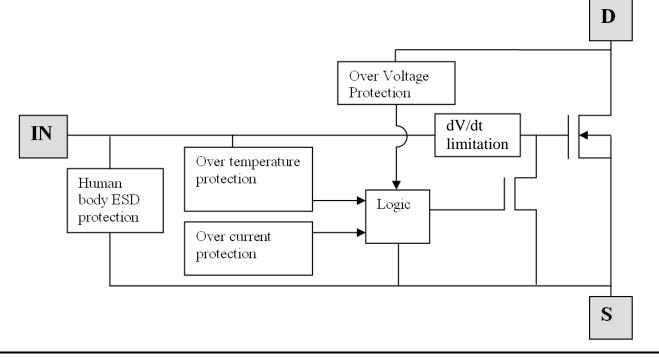
Marking Information



6004N8 = Product Name YY: Year WW: Week: 01~52; 52 represents 52 and 53 week



Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V
Continuous Input Voltage	VIN	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} < -0.2V or V _{IN} > 6V	l _{iN}	No limit │ I _{IN} │ ≤ 2	mA
Pulsed Drain Current @VIN = 3.3V	I _{DM}	2	А
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	2.5	А
Continuous Source Current (Body Diode) (Note 5)	I _S	1	А
Pulsed Source Current (Body Diode)	I _{SM}	5	А
Unclamped Single Pulse Inductive Energy, $T_J = +25^{\circ}C$, $I_D = 0.5A$, $V_{DD} = 24V$	E _{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V _{HBM}	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Thermal Resistance (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	1.28 10	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	P _D	1.65 12.4	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	76	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	12	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Thermal resistance between junction and the mounting surfaces of drain and source pins.



Recommended Operating Conditions

The ZXMS6004N8Q is optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	VIN	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be on	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	VP	0	36	V

Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

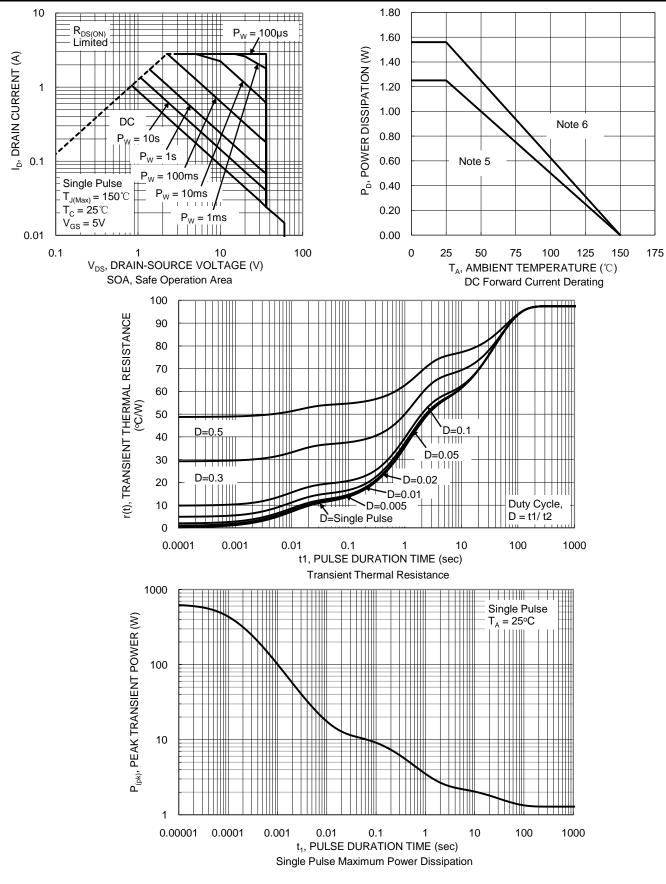
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics			71			
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	$I_D = 10 \text{mA}$
Off State Drain Current	IDSS	-	-	0.5	μA	$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current		-	-	1		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	VIN(TH)	0.7	1	1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$
Innut Current		-	60	100		$V_{IN} = 3V$
Input Current	I _{IN}	-	120	200	μA	$V_{IN} = 5V$
Input Current While Over-Temperature Active	-	-	-	400	μA	$V_{IN} = 5V$
Static Drain-Source On-State Resistance	D	-	400	600		$V_{IN} = 3V, I_D = 0.5A$
Static Drain-Source On-State Resistance	R _{DS(ON)}	-	350	500	mΩ	$V_{IN} = 5V, I_D = 0.5A$
Continuous Drain Current (Note E)	— I _D	0.9	-	-		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 5)		1.0	-	-	A	$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.2	-	-		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.3	-	-		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 9)	I _{D(LIM)}	0.7	1.7	-	A	$V_{IN} = 3V$
Current Limit (Note 8)		1	2.2	-		$V_{IN} = 5V$
Dynamic Characteristics	•		•			
Turn On Delay Time	t _{D(ON)}	-	5	-		
Rise Time	t _R	-	10	-		V_{DD} = 12V, I_D = 0.5A, V_{GS} = 5V
Turn Off Delay Time	t _{D(OFF)}	-	45	-	μs	
Fall Time	tF	_	15	-		
Over-Temperature Protection	•			-		·
Thermal Overload Trip Temperature (Note 9)	T _{JT}	+150	+175	-	°C	-
Thermal Hysteresis (Note 9)	ΔT_{JT}	-	+10	-	°C	_

Notes: 8. The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

9. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.



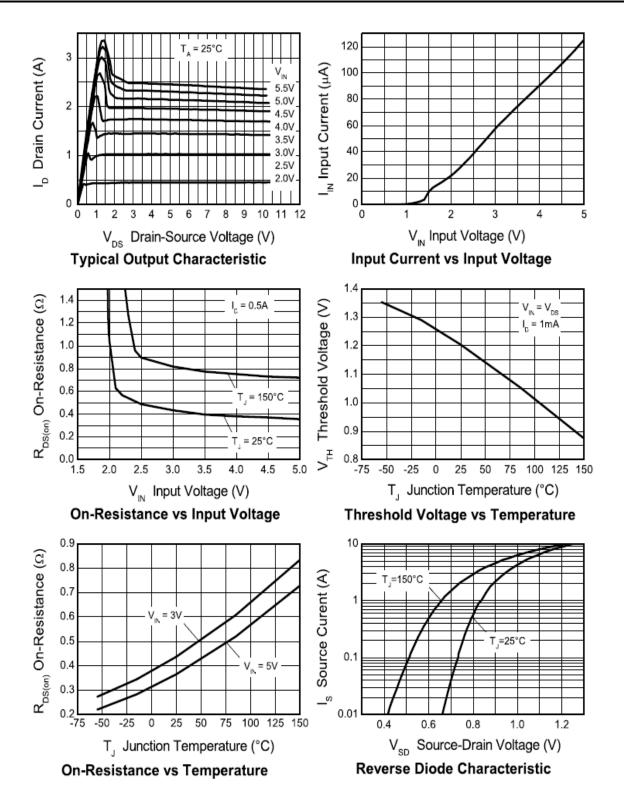
Thermal Characteristics



IntelliFET is a registered trademark of Diodes Incorporated. ZXMS6004N8Q Document number: DS38897 Rev. 2 - 2

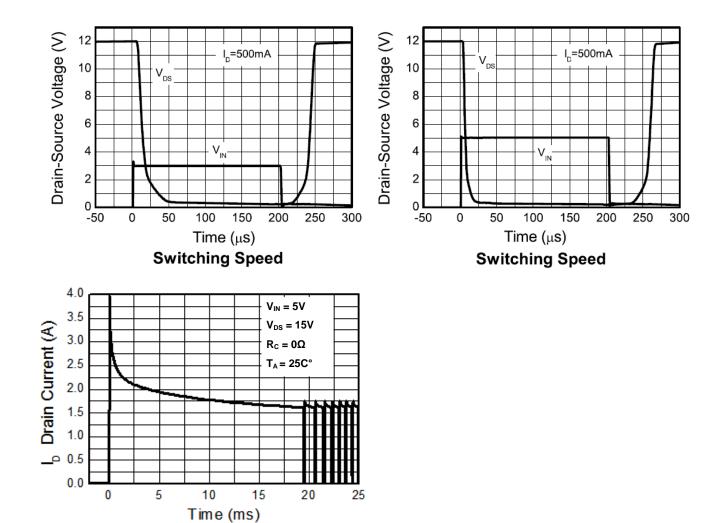


Typical Characteristics





Typical Characteristics (Cont.)



Typical Short Circuit Protection

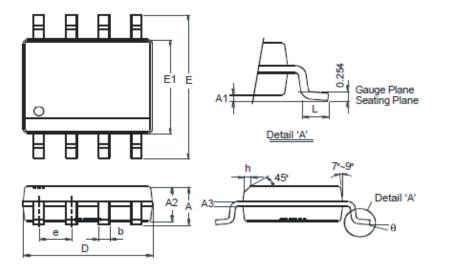


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

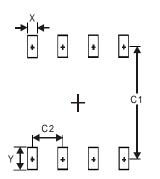
SO-8



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27	Тур		
h	- 0.35			
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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